

N-channel TrenchMOS logic level FET

19 March 2014

Product data sheet

### 1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 2. Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources

### 3. Applications

- 12 V, 24 V and 42 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

### 4. Quick reference data

| Table 1. Q           | uick reference data                                 |  |     |     |     |      |
|----------------------|---|--|-----|-----|-----|------|
| Symbol               | Parameter   | Conditions   | Min | Тур | Max | Unit |
| V <sub>DS</sub>      | drain-source voltage                                | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C  | -   | -   | 100 | V    |
| I <sub>D</sub>       | drain current                                       | V <sub>GS</sub> = 5 V; T <sub>sp</sub> = 25 °C; <u>Fig. 2; Fig. 3</u>  | -   | -   | 7   | А    |
| P <sub>tot</sub>     | total power dissipation                             | T <sub>sp</sub> = 25 °C; <u>Fig. 1</u>   | -   | -   | 8   | W    |
| Static chara         | acteristics   | · · · · · ·  |     |     |     |      |
| R <sub>DSon</sub>    | drain-source on-state                               | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C  | -   | -   | 84  | mΩ   |
|                      | resistance  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C   | -   | 62  | 72  | mΩ   |
|                      |   | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 12;</u><br><u>Fig. 13</u>   | -   | 64  | 75  | mΩ   |
| Avalanche r          | ruggedness  | ·  |     |     |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-<br>source avalanche<br>energy | $\begin{split} I_D &= 7 \text{ A};  \text{V}_{\text{sup}} \leq 100 \text{ V};  \text{R}_{\text{GS}} = 50  \Omega; \\ \text{V}_{\text{GS}} &= 5 \text{ V};  \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped} \end{split}$ | -   | -   | 49  | mJ   |

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### 5. Pinning information

| Table 2. | Pinning | information |                            |                |
|----------|---------|-------------|----------------------------|----------------|
| Pin      | Symbol  | Description | Simplified outline         | Graphic symbol |
| 1        | G       | gate        | 4                          | D              |
| 2        | D       | drain       |                            |                |
| 3        | S       | source      |                            | G-UFT 4        |
| 4        | D       | drain       | L1 L2 L3<br>SC-73 (SOT223) | mbb076 S       |

### 6. Ordering information

| Table 3. Ordering in | formation |  |         |  |  |  |
|----------------------|-----------|--|---------|--|--|--|
| Type number          | Package   |  |         |  |  |  |
|                      | Name      | Description  | Version |  |  |  |
| BUK9875-100A         | SC-73     | plastic surface-mounted package with increased heatsink; 4 leads | SOT223  |  |  |  |
| BUK9875-100A/CU      | SC-73     | plastic surface-mounted package with increased heatsink; 4 leads | SOT223  |  |  |  |

# 7. Marking

| Table 4. Marking codes |              |
|------------------------|--------------|
| Type number            | Marking code |
| BUK9875-100A           | 987510A      |
| BUK9875-100A/CU        | 987510       |

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter               | Conditions  | Min | Max | Unit |
|------------------|-------------------------|---|-----|-----|------|
| V <sub>DS</sub>  | drain-source voltage    | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C                       | -   | 100 | V    |
| V <sub>DGR</sub> | drain-gate voltage      | R <sub>GS</sub> = 20 kΩ   | -   | 100 | V    |
| V <sub>GS</sub>  | gate-source voltage     |   | -10 | 10  | V    |
| P <sub>tot</sub> | total power dissipation | T <sub>sp</sub> = 25 °C; <u>Fig. 1</u>                                | -   | 8   | W    |
| I <sub>D</sub>   | drain current           | T <sub>sp</sub> = 25 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2; Fig. 3</u> | -   | 7   | А    |
|                  |                         | T <sub>sp</sub> = 100 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2</u>        | -   | 4   | А    |
| I <sub>DM</sub>  | peak drain current      | $T_{sp}$ = 25 °C; pulsed; $t_p \le 10 \ \mu s$ ; Fig. 3               | -   | 28  | А    |

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| Symbol               | Parameter                                    | Conditions   | Min | Мах | Unit |
|----------------------|--|--|-----|-----|------|
| T <sub>stg</sub>     | storage temperature                          |  | -55 | 150 | °C   |
| Tj                   | junction temperature                         |  | -55 | 150 | °C   |
| V <sub>GSM</sub>     | peak gate-source voltage                     | pulsed; $t_p \le 50 \ \mu s$   | -15 | 15  | V    |
| Source-drai          | in diode                                     |  |     |     |      |
| I <sub>S</sub>       | source current                               | T <sub>sp</sub> = 25 °C  | -   | 7   | А    |
| I <sub>SM</sub>      | peak source current                          | pulsed; $t_p \le 10 \ \mu s$ ; $T_{sp} = 25 \ ^\circ C$  | -   | 28  | А    |
| Avalanche i          | ruggedness                                   | · · ·  |     |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | $\begin{split} I_D = 7 \text{ A}; \ V_{sup} &\leq 100 \text{ V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} &= 5 \text{ V}; \ T_{j(init)} = 25 \ ^\circ\text{C}; \ unclamped \end{split}$ | -   | 49  | mJ   |

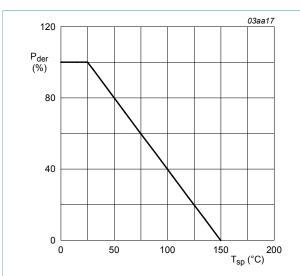


Fig. 1. Normalized total power dissipation as a function of solder point temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

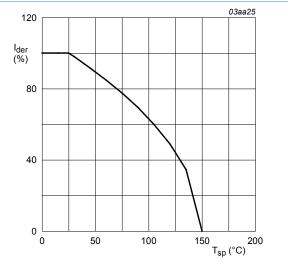
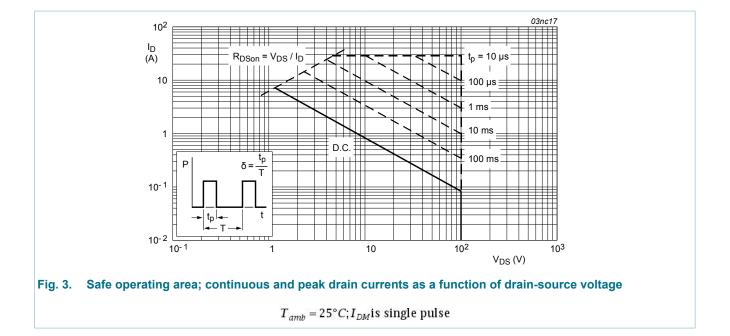


Fig. 2. Normalized continuous drain current as a function of solder point temperature

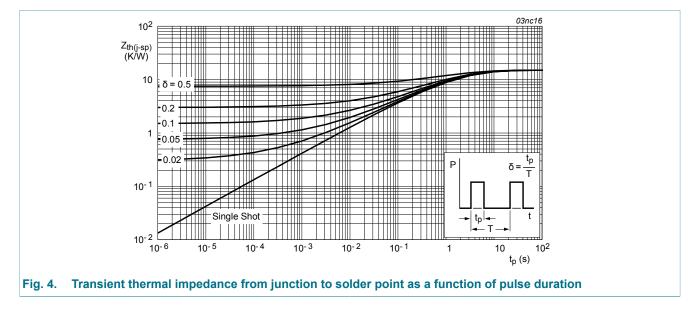
$$I_{der} = \frac{I_D}{I_{D(25^\circ \text{C})}} \times 100\%$$

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### 9. Thermal characteristics

| Table 6. Thermal characteristics |  |               |  |     |     |     |      |
|----------------------------------|--|---------------|--|-----|-----|-----|------|
| Symbol                           | Parameter  | Conditions    |  | Min | Тур | Max | Unit |
| R <sub>th(j-sp)</sub>            | thermal resistance<br>from junction to solder<br>point |               |  | -   | -   | 15  | K/W  |
| R <sub>th(j-a)</sub>             | thermal resistance<br>from junction to<br>ambient      | <u>Fig. 4</u> |  | -   | 120 | -   | K/W  |



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# **10. Characteristics**

| Symbol               | Parameter                           | Conditions  | Min | Тур  | Max  | Unit |
|----------------------|-------------------------------------|---|-----|------|------|------|
| Static chara         | cteristics                          |   |     |      |      |      |
| V <sub>(BR)DSS</sub> | drain-source                        | I <sub>D</sub> = 0.25 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                                 | 100 | -    | -    | V    |
|                      | breakdown voltage                   | I <sub>D</sub> = 0.25 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C                                | 89  | -    | -    | V    |
| V <sub>GS(th)</sub>  | gate-source threshold voltage       | I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 25 °C;<br><u>Fig. 11</u>    | 1   | 1.5  | 2    | V    |
|                      |                                     | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C;<br>Fig. 11  | -   | -    | 2.3  | V    |
|                      |                                     | $I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 150 °C;<br>Fig. 11  | 0.6 | -    | -    | V    |
| I <sub>DSS</sub>     | drain leakage current               | $V_{DS}$ = 100 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C   | -   | 0.05 | 10   | μA   |
|                      |                                     | V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C                                 | -   | -    | 500  | μA   |
| I <sub>GSS</sub>     | gate leakage current                | $V_{GS}$ = 10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C  | -   | 2    | 100  | nA   |
|                      |                                     | $V_{GS}$ = -10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C   | -   | 2    | 100  | nA   |
| R <sub>DSon</sub>    | drain-source on-state<br>resistance | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 150 °C;<br>Fig. 12; Fig. 13               | -   | -    | 162  | mΩ   |
|                      |                                     | V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C                                   | -   | -    | 84   | mΩ   |
|                      |                                     | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C                                    | -   | 62   | 72   | mΩ   |
|                      |                                     | V <sub>GS</sub> = 5 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u> ;<br><u>Fig. 13</u> | -   | 64   | 75   | mΩ   |
| Dynamic ch           | aracteristics                       | · · · · · · · · · · · · · · · · · · ·   | I   |      |      |      |
| C <sub>iss</sub>     | input capacitance                   | V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;   | -   | 1270 | 1690 | pF   |
| C <sub>oss</sub>     | output capacitance                  | T <sub>j</sub> = 25 °C; <u>Fig. 14</u>  | -   | 140  | 167  | pF   |
| C <sub>rss</sub>     | reverse transfer capacitance        |   | -   | 90   | 124  | pF   |
| d(on)                | turn-on delay time                  | $V_{DS}$ = 30 V; R <sub>L</sub> = 1.2 Ω; V <sub>GS</sub> = 5 V;   | -   | 13   | -    | ns   |
| tr                   | rise time                           | R <sub>G(ext)</sub> = 10 Ω; T <sub>j</sub> = 25 °C  | -   | 120  | -    | ns   |
| d(off)               | turn-off delay time                 |   | -   | 58   | -    | ns   |
| f                    | fall time                           |   | -   | 57   | -    | ns   |
| Source-drai          | n diode                             | · · · · · · · · · · · · · · · · · · ·   | 1   |      |      | ,    |
| V <sub>SD</sub>      | source-drain voltage                | I <sub>S</sub> = 5 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <u>Fig. 15</u>                     | -   | 0.85 | 1.2  | V    |
| t <sub>rr</sub>      | reverse recovery time               | I <sub>S</sub> = 20 A; dI <sub>S</sub> /dt = -100 A/μs;   | -   | 63   | -    | ns   |
| Q <sub>r</sub>       | recovered charge                    | $V_{GS}$ = -10 V; $V_{DS}$ = 30 V; $T_j$ = 25 °C  | -   | 220  | -    | nC   |

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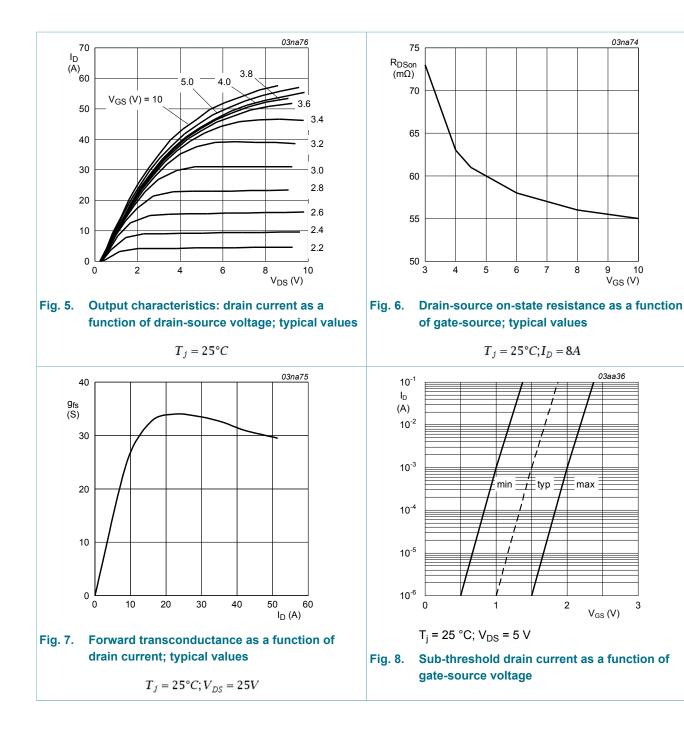
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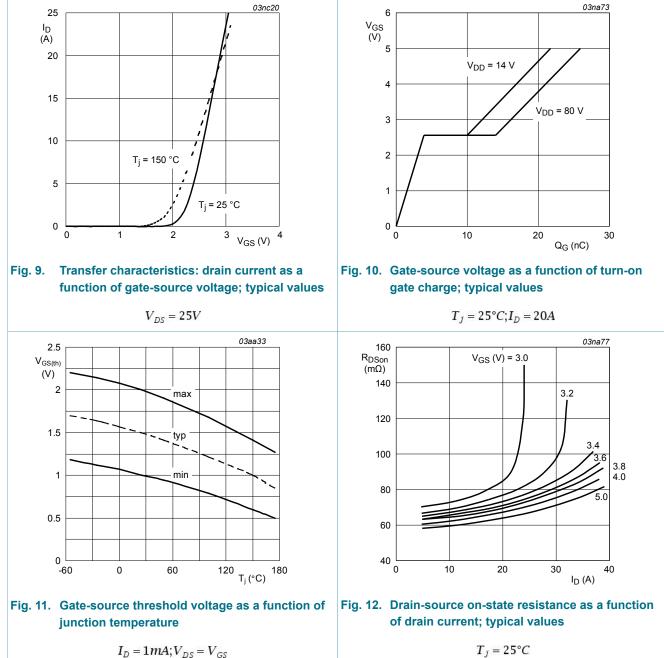
10  $V_{GS}(V)$ 

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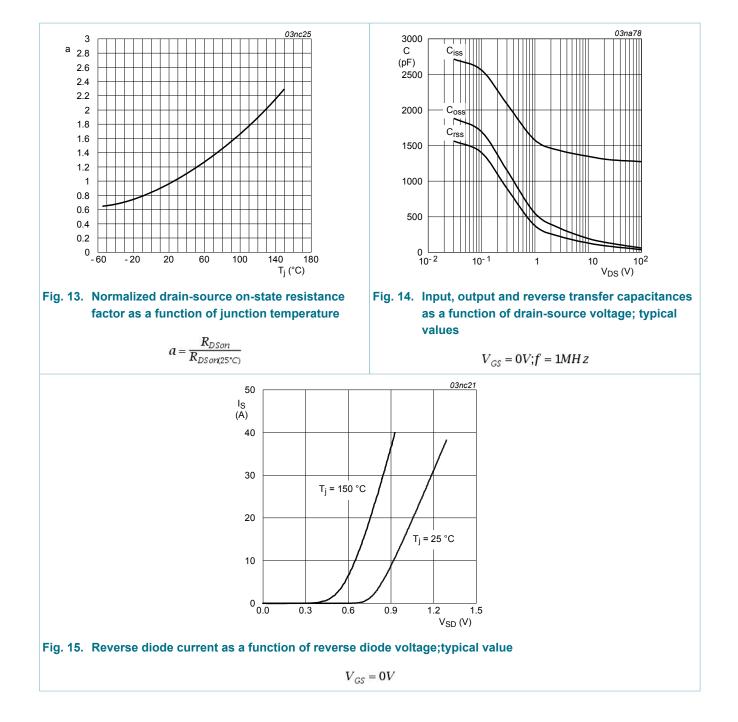


 $I_D = 1 m A; V_{DS} = V_{GS}$ 



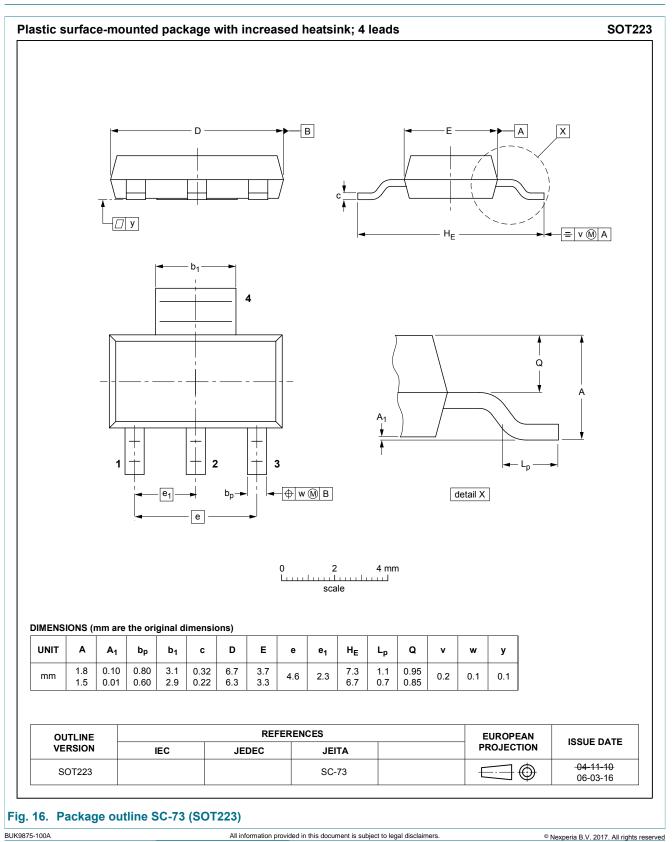
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### 11. Package outline



**Product data sheet** 

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### 12. Legal information

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| Document status [1][2]               | Product<br>status [ <u>3]</u> | Definition  |
|--------------------------------------|-------------------------------|---|
| Objective<br>[short] data<br>sheet   | Development                   | This document contains data from<br>the objective specification for product<br>development. |
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